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April 2015

FDMC86262P

P-Channel PowerTrench[®] MOSFET -150 V, -2 A, 307 mΩ

Features

- Max $r_{DS(on)}$ = 307 mΩ at $V_{GS} = -10$ V, $I_D = -2$ A
- Max $r_{DS(on)}$ = 356 mΩ at $V_{GS} = -6$ V, $I_D = -1.8$ A
- Very Low $r_{DS(on)}$ Mid Voltage P-Channel Silicon Technology Optimised for Low Qg
- Optimised for Fast Switching Applications as well as Load Switch Applications
- 100% UIL Tested
- RoHS Compliant

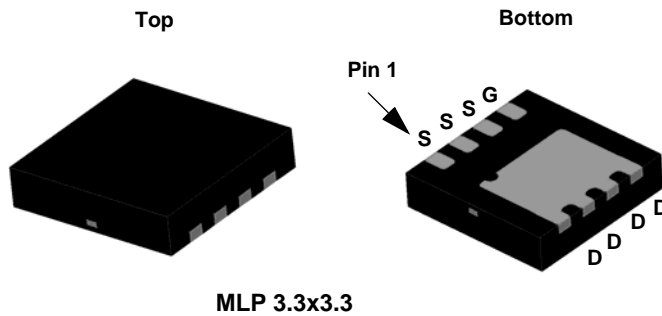


General Description

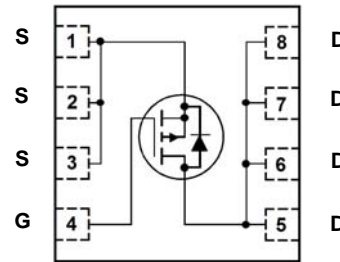
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] technology. This very high density process is especially tailored to minimize on-state resistance and optimized for superior switching performance.

Applications

- Active Clamp Switch
- Load Switch



MLP 3.3x3.3



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	-150	V
V_{GS}	Gate to Source Voltage	± 25	V
I_D	Drain Current -Continuous	$T_C = 25^\circ\text{C}$ (Note 5)	-8.4
	-Continuous	$T_C = 100^\circ\text{C}$ (Note 5)	-5.3
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	-2
	-Pulsed	(Note 4)	-35
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	37
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	40
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.3
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86262P	FDMC86262P	Power 33	13"	12 mm	3000 units

FDMC86262P P-Channel PowerTrench[®] MOSFET

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu\text{A}, V_{GS} = 0 \text{ V}$	-150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C		-86		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -120 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu\text{A}$	-2	-2.9	-4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C		5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10 \text{ V}, I_D = -2 \text{ A}$		241	307	m Ω
		$V_{GS} = -6 \text{ V}, I_D = -1.8 \text{ A}$		266	356	
		$V_{GS} = -10 \text{ V}, I_D = -2 \text{ A}, T_J = 125^\circ\text{C}$		425	541	
g_{FS}	Forward Transconductance	$V_{DS} = -10 \text{ V}, I_D = -2 \text{ A}$		5.4		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		632	885	pF
C_{oss}	Output Capacitance			45	65	pF
C_{rss}	Reverse Transfer Capacitance			1.3	2.0	pF
R_g	Gate Resistance		0.1	3	6	Ω

Switching Characteristics

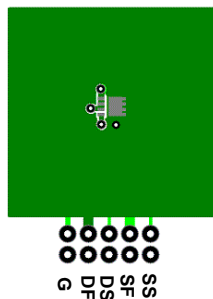
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -75 \text{ V}, I_D = -2 \text{ A}, V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$		8.5	17	ns	
t_r	Rise Time			2.2	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			15	26	ns	
t_f	Fall Time			5.6	11	ns	
Q_g	Total Gate Charge		$V_{GS} = 0 \text{ V to } -10 \text{ V}$		9.1	13	nC
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V to } -6 \text{ V}$	$V_{DD} = -75 \text{ V}, I_D = -2 \text{ A}$		5.6	7.9	nC
Q_{gs}	Gate to Source Charge				2.5		nC
Q_{gd}	Gate to Drain "Miller" Charge				1.6		nC

Drain-Source Diode Characteristics

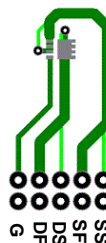
V_{SD}	Source-Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2 \text{ A}$ (Note 2)		-0.8	-1.3	V
t_{rr}	Reverse Recovery Time	$I_F = -2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		72	116	ns
Q_{rr}	Reverse Recovery Charge			166	266	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $53^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. Starting $T_J = 25^\circ\text{C}$, $L = 3 \text{ mH}$, $I_{AS} = -5 \text{ A}$, $V_{DD} = -150 \text{ V}$, $V_{GS} = -10 \text{ V}$.

4. Pulsed Id please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

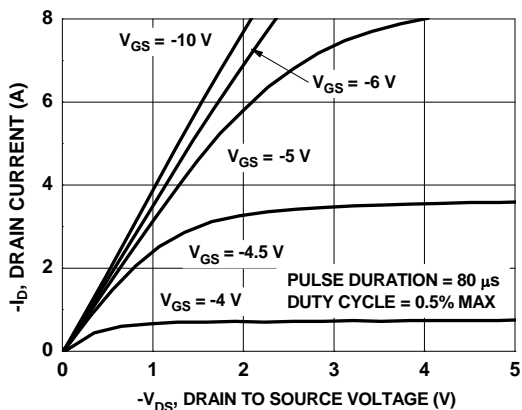


Figure 1. On Region Characteristics

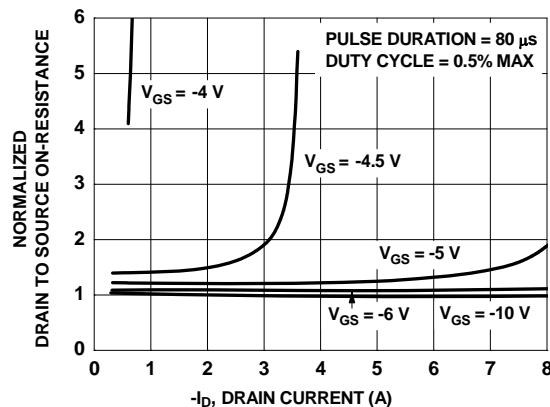


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

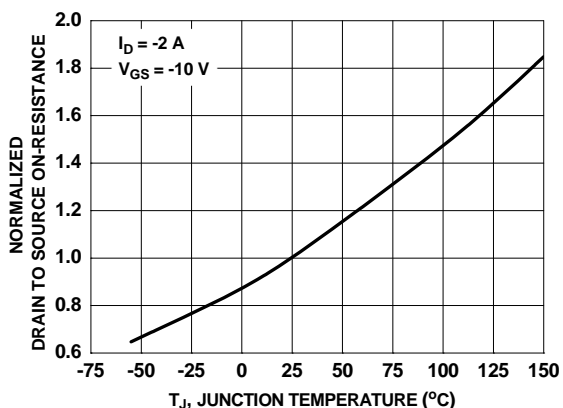


Figure 3. Normalized On Resistance vs. Junction Temperature

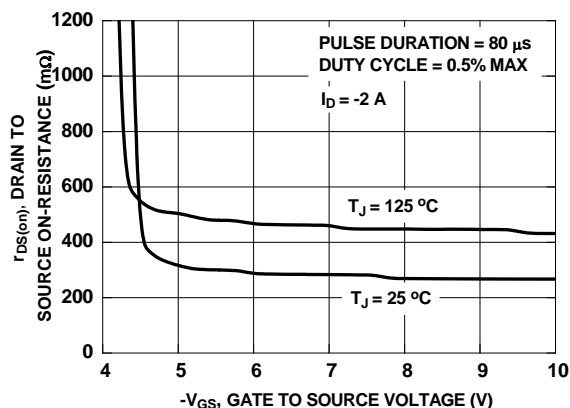


Figure 4. On-Resistance vs. Gate to Source Voltage

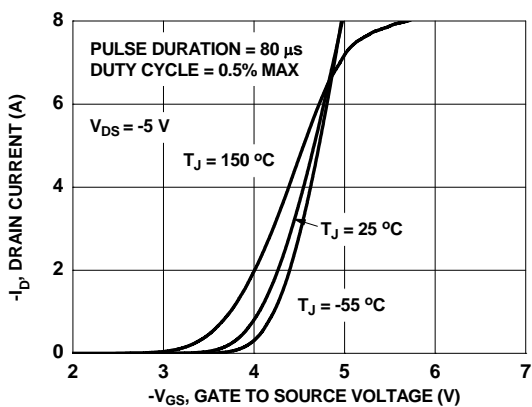


Figure 5. Transfer Characteristics

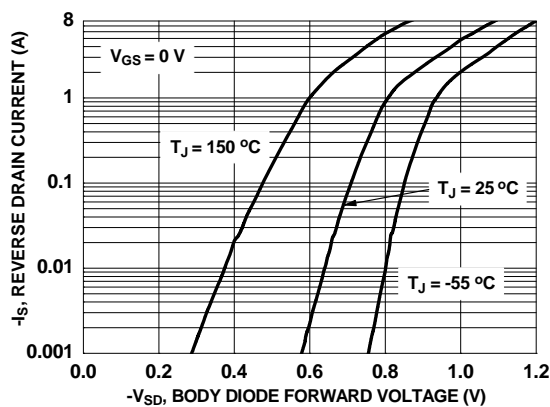


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

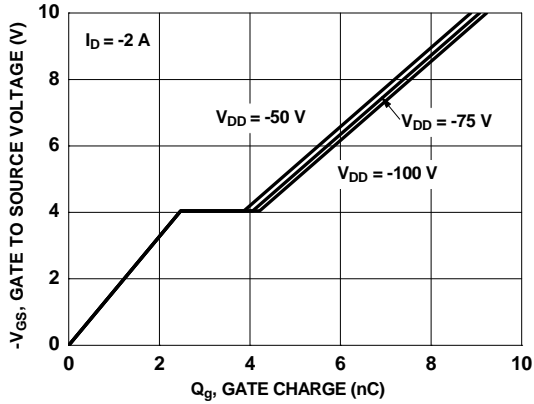


Figure 7. Gate Charge Characteristics

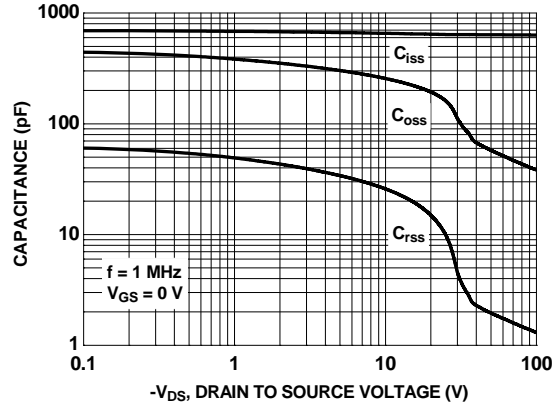


Figure 8. Capacitance vs. Drain to Source Voltage

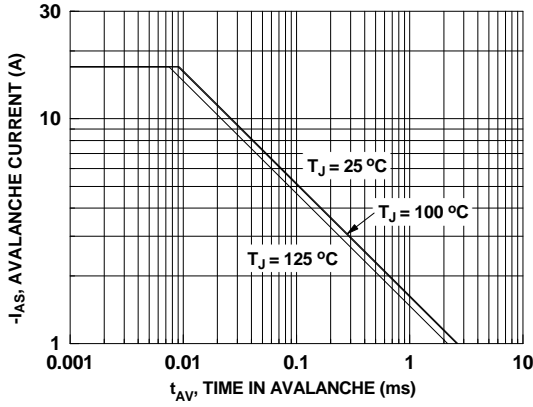


Figure 9. Unclamped Inductive Switching Capability

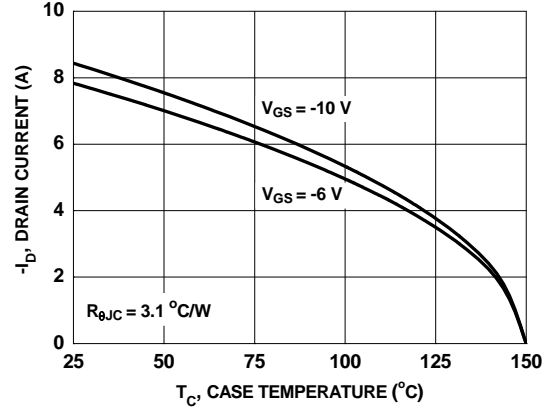


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

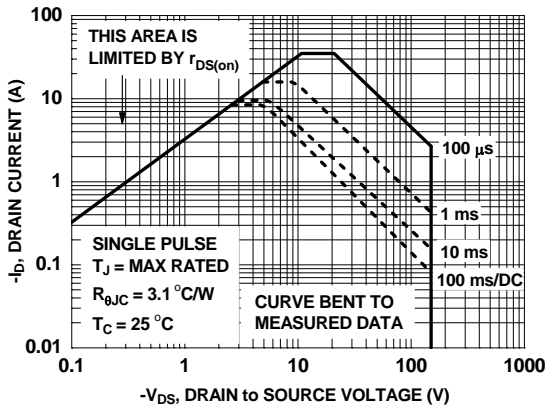


Figure 11. Forward Bias Safe Operating Area

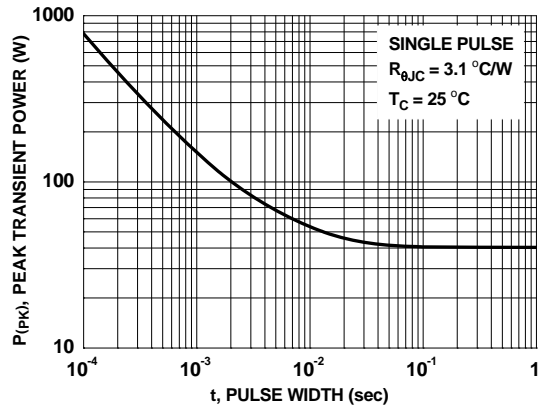


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

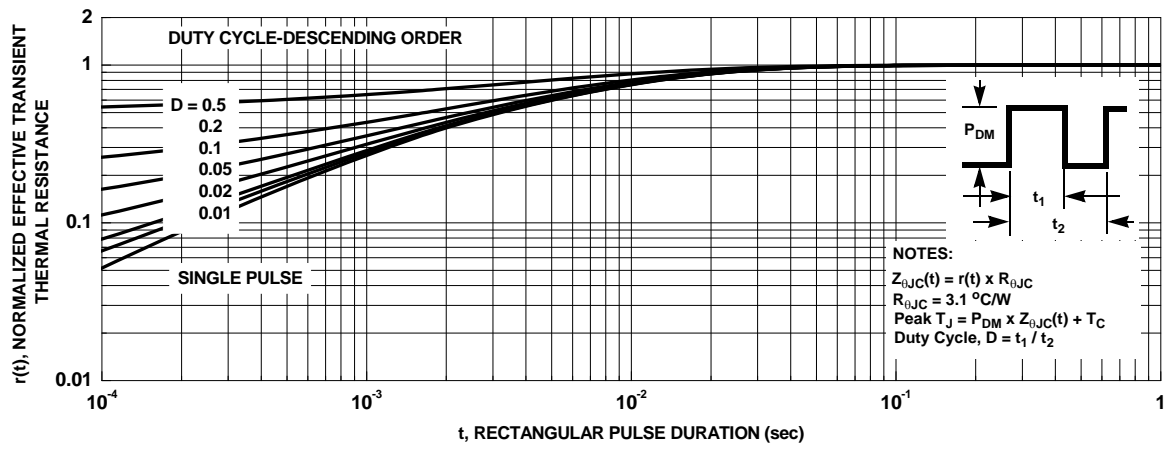
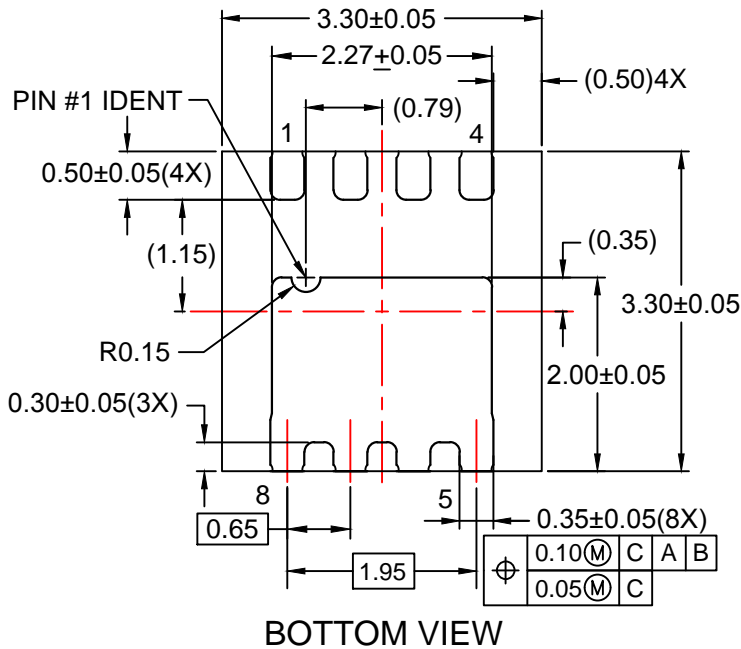


Figure 13. Junction-to-Case Transient Thermal Response Curve



NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP08Srev3.



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